50V~1000V 1.0A DO-41

General purpose silicon rectifier Reverse Voltage 50 to1000V Forward Current 1.0A DO-41 axial package.

Plated axial lead, Low reverse leakage, High forward surge current capability.

General purpose.

PIN1 Cathode PIN2:Anode

See Marking Instructions.

| Parameter | Symbol | Rating | | | | | | | Unit |
|---|---|---|---|---|---|---|---|---|---|
| | | 1N4001G | 1N4002G | 1N4003G | 1N4004G | 1N4005G | 1N4006G | 1N4007G | |
| Maximum Recurrent Peak Reverse Voltage | $V_{RRM}$ | 50 | 100 | 200 | 400 | 600 | 800 | 1000 | V |
| Maximum RMS Voltage | $V_{RMS}$ | 35 | 70 | 140 | 280 | 420 | 560 | 700 | V |
| Maximum DC Blocking Voltage | $V_{DC}$ | 50 | 100 | 200 | 400 | 600 | 800 | 1000 | V |
| Maximum average forward rectified current 0.375"(9.5mm) lead length at $T_A$=75 C | $I_{F\ AV}$ | 1.0 | | | | | | | A |
| Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method) | $I_{FSM}$ | 30.0 | | | | | | | A |
| Typical Junction Capacitance [1] | $C_j$ | 15.0 | | | | | | | pF |
| Typical Thermal Resistance[2)] | $R_{\theta JA}$ | 50.0 | | | | | | | /W |
| Operating and Storage Temperature Range | $T_j$,$T_{stg}$ | -55~+150 | | | | | | | |

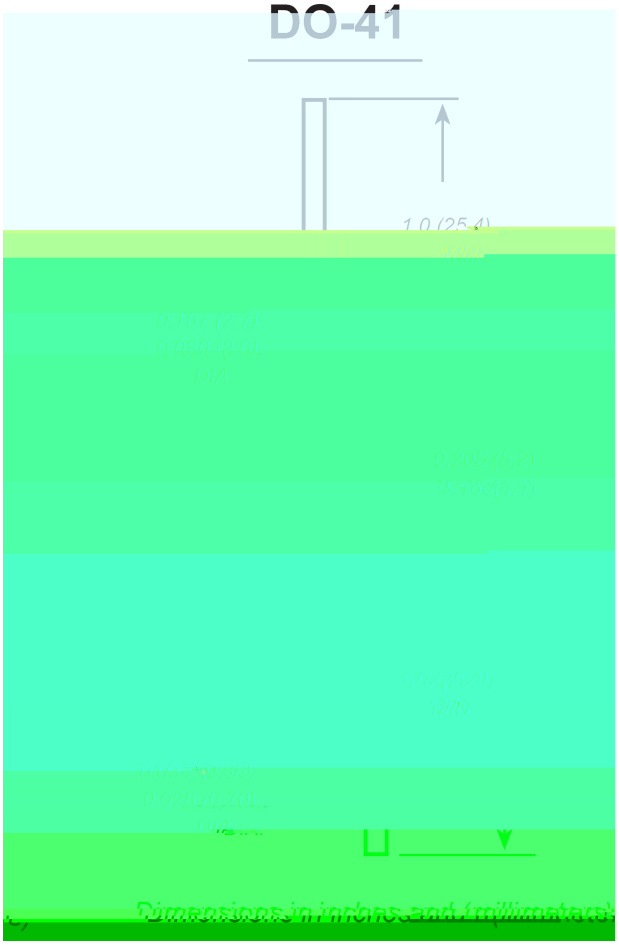
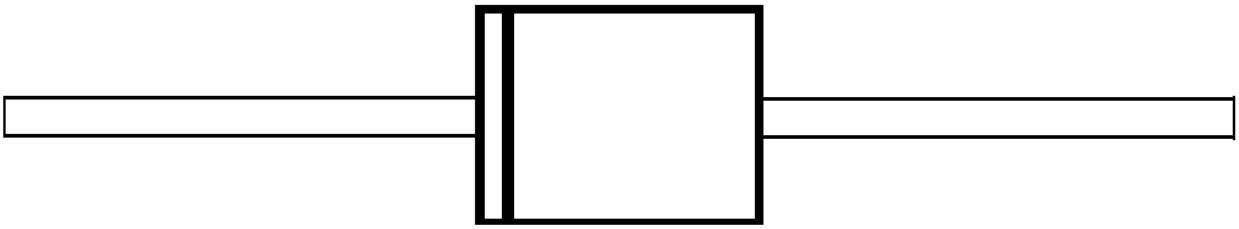
Note:

1) Measured at 1MHz and applied reverse voltage of 4.0V D.C.

2) Thermal resistance from junction to ambient at 0.375" (9.5mm)lead length,P.C.B. mounted.

| Parameter | Symbol | Test Conditions | Rating | | | | | | | Unit |
|---|---|---|---|---|---|---|---|---|---|---|
| | | | 1N4001G | 1N4002G | 1N4003G | 1N4004G | 1N4005G | 1N4006G | 1N4007G | |
| Maximum Instantaneous Forward Voltage | $V_F$ | $I_F$=1.0A | 1.1 | | | | | | | V |
| Maximum DC Reverse Current at Maximum DC Blocking Voltage | $I_R$ | $T_A$=25 | 5.0 | | | | | | | μA |
| | | $T_A$=125 | 50.0 | | | | | | | μA |

# DO-41


1.0 (25.4)
MIN.
0.107 (2.7)
0.080 (2.0)
DIA.
0.205 (5.2)
0.160 (4.1)
1.0 (25.4)
MIN.
0.034 (0.86)
0.028 (0.71)
DIA.
Dimensions in inches and (millimeters)